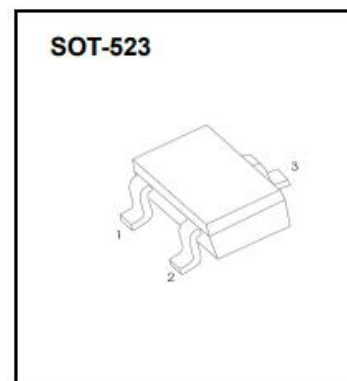
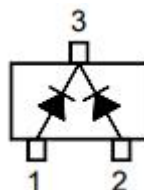


Schottky Barrier Diode

Features

- Low current rectification

Marking Code: **3D**

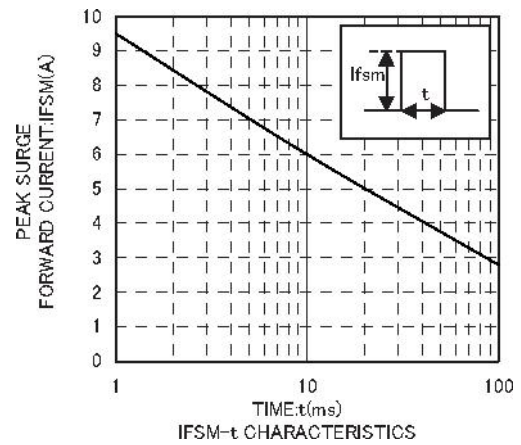
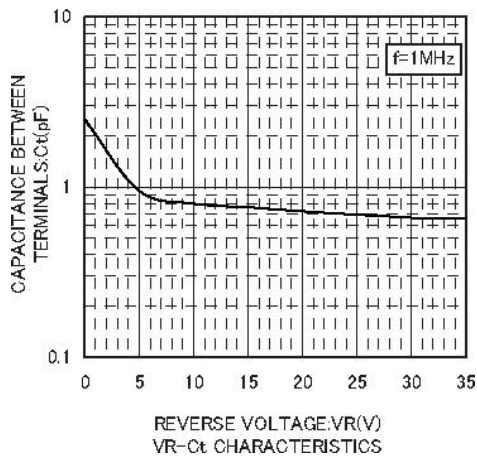
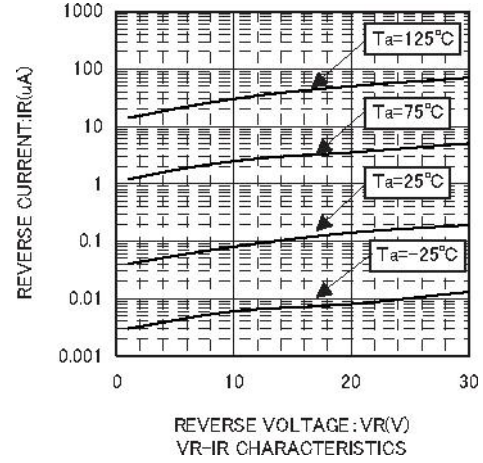
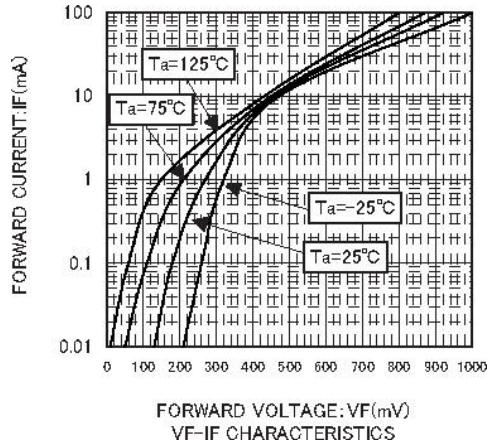


Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	V _{RM}	40	V
Reverse Voltage	V _R	40	V
Average Rectified Forward Current	I _{F(AV)}	30	mA
Peak Forward Surge Current (t = 8.3 ms)	I _{FSM}	200	mA
Junction Temperature	T _j	125	°C
Storage Temperature Range	T _{stg}	- 55 to + 125	°C

Characteristics at T_a = 25 °C

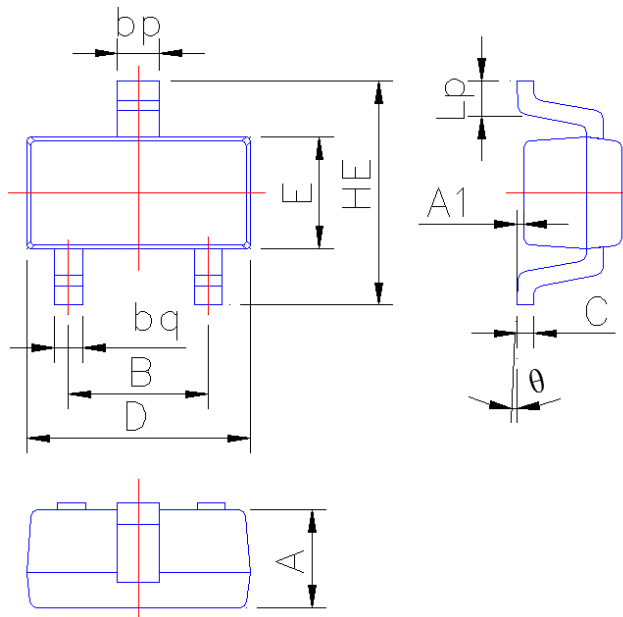
Parameter	Symbol	Min.	Typ.	Max.	Unit
Forward Voltage at I _F = 1 mA	V _F	-	-	0.37	V
Reverse Breakdown Voltage at I _R = 10 μA	V _{(BR)R}	40	-	-	V
Reverse Current at V _R = 10 V	I _R	-	-	1	μA
Capacitance between Terminals at V _R = 1 V, f = 1 MHz	C _t	-	2	-	pF



PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT-523



Symbol	Dimension in Millimeters	
	Min	Max
A	0.60	0.80
A1	0.010	0.100
B	0.95	1.05
bp	0.26	0.40
bq	0.16	0.30
C	0.09	0.15
D	1.50	1.70
E	0.70	0.85
HE	1.45	1.75
Lp	0.16	0.36
θ	0°	5°